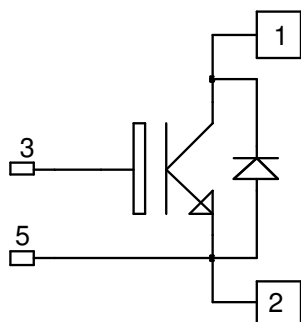


Single switch Trench IGBT® Power Module

$V_{CES} = 1200V$
 $I_C = 200A$ @ $T_c = 80^\circ C$



Application

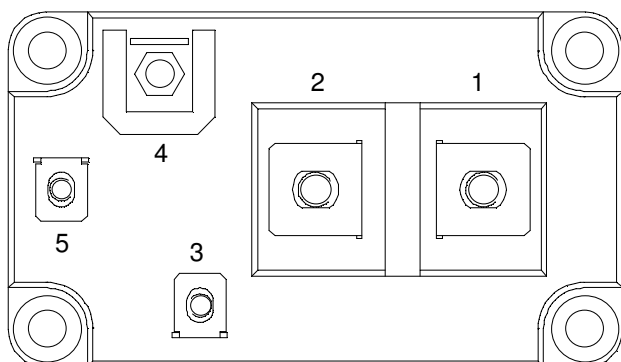
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
 - M6 connectors for power
 - M4 connectors for signal
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of V_{CEsat}



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	300
		$T_c = 80^\circ C$	200
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	400
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	1040
RBSOA	Reverse Bias Safe Operating Area	$T_J = 125^\circ C$	400A @ 1100V



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
BV _{CES}	Collector - Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 8mA		1200			V
I _{CES}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 1200V				20	mA
V _{CE(on)}	Collector Emitter on Voltage	V _{GE} = 15V I _C = 200A	T _j = 25°C	1.4	1.7	2.1	V
			T _j = 125°C		2.0		
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 8mA		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V				1200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		14.4		nF
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.65		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 200A$ $R_G = 4.7\Omega$		150		ns
T_r	Rise Time			90		
$T_{d(off)}$	Turn-off Delay Time			550		
T_f	Fall Time			130		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 200A$ $R_G = 4.7\Omega$		180		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			180		
E_{off}	Turn off Energy			26		mJ

Reverse diode ratings and characteristics

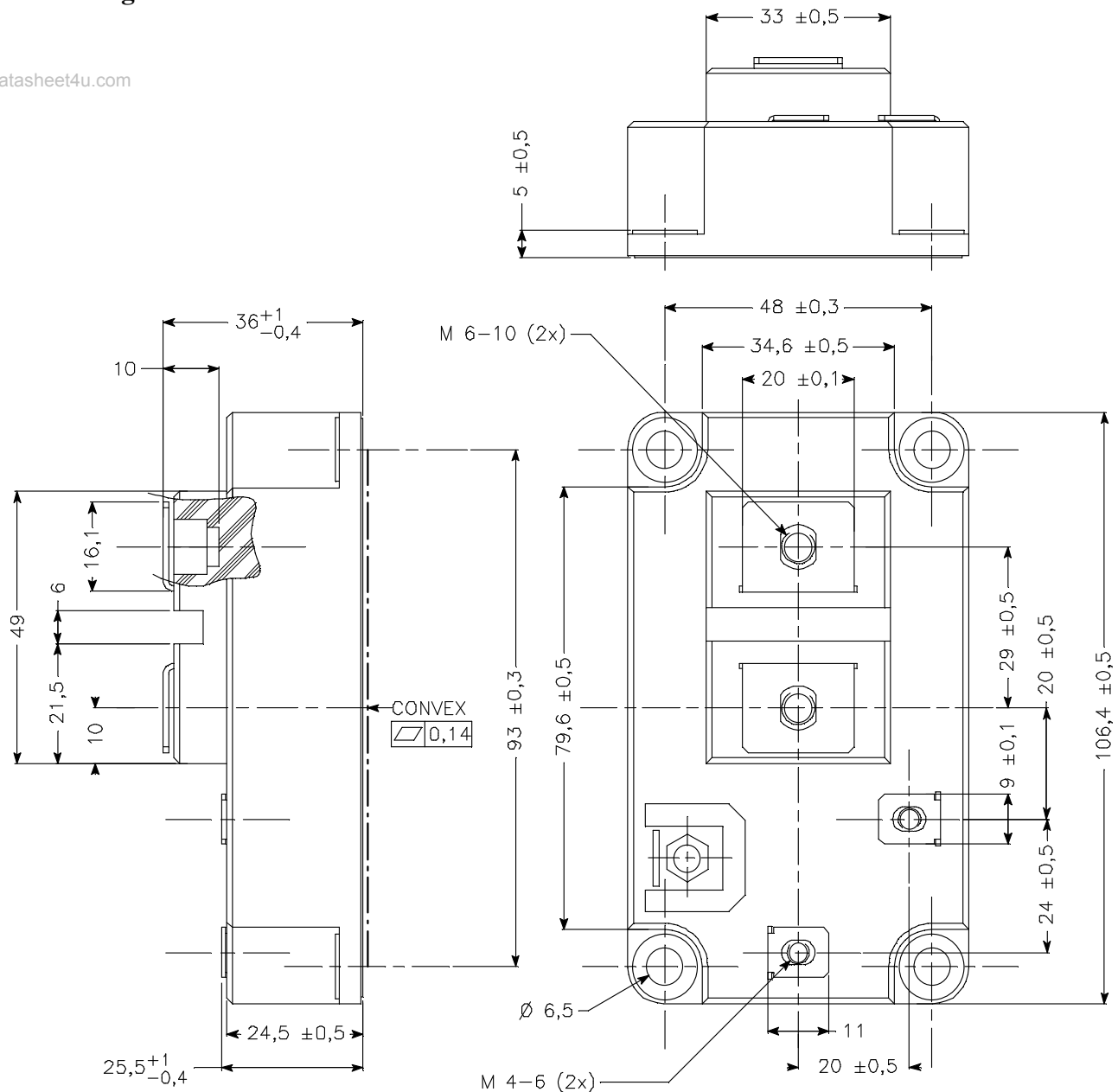
V_F	Forward Voltage	$V_{GE} = 0V$ $I_F = 200A$	$T_j = 25^\circ\text{C}$		1.6	2.2	V
			$T_j = 125^\circ\text{C}$		1.6		
E_{rec}	Reverse Recovery Energy	$I_F = 200A$ $V_R = 600V$ $di/dt = 990A/\mu s$	$T_j = 125^\circ\text{C}$		16		mJ
Q_{rr}	Reverse Recovery Charge	$I_F = 200A$ $V_R = 600V$ $di/dt = 990A/\mu s$	$T_j = 25^\circ\text{C}$		20.8		μC
			$T_j = 125^\circ\text{C}$		38		

Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit
R_{thJC}	Junction to Case	IGBT			0.12	$^\circ\text{C/W}$
		Diode			0.19	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1$ min, $I_{isol} < 1mA, 50/60Hz$		2500			V
T_j	Operating junction temperature range		-40		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		125	
Torque	Mounting torque	M6	3		5	N.m
		M4	1		2	
Wt	Package Weight				420	g

Package outline

www.datasheet4u.com



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.